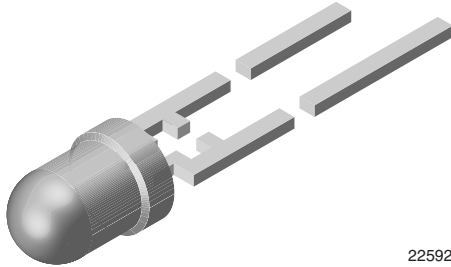


## Infrared Emitting Diode, 950 nm, GaAs



22592

### DESCRIPTION

TSUS3400 is an infrared, 950 nm emitting diode in GaAs technology, molded in a clear, blue tinted plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm):  $\varnothing$  3
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- Angle of half intensity:  $\varphi = \pm 18^\circ$
- Low forward voltage
- Radiant power: 20 mW at  $I_F = 100$  mA
- Suitable for DC and high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance with WEEE 2002/96/EC



### Note

\*\* Please see document "Vishay Material Category Policy": [www.vishay.com/doc?99902](http://www.vishay.com/doc?99902)

### APPLICATIONS

- Infrared source in photo interrupters, reflective and transmissive sensors

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSUS3400	15	$\pm 18$	950	800

### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS3400	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	$I_{FSM}$	2	A
Power dissipation		$P_V$	170	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction/ambient		$R_{thJA}$	450	K/W

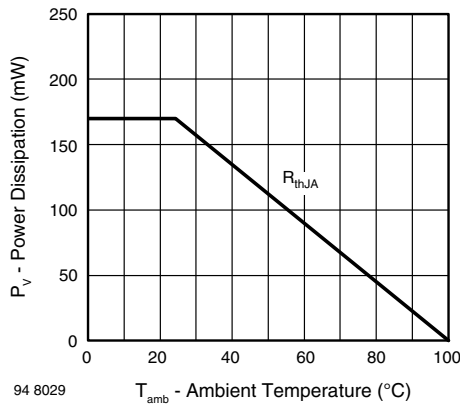


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

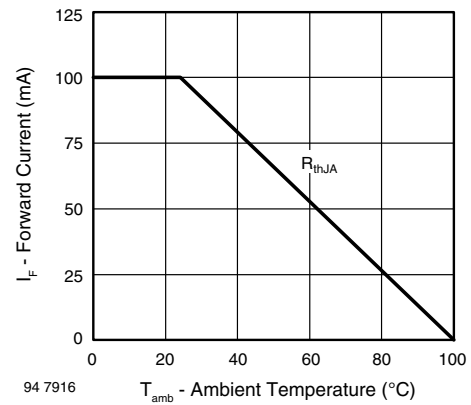


Fig. 2 - Forward Current vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$V_F$		1.3	1.7	V
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$		2.2		V
Temperature coefficient of $V_F$	$I_F = 100\text{ mA}$	$TK_{V_F}$		-1.3		mV/K
Reverse current	$V_R = 5\text{ V}$	$I_R$			100	$\mu\text{A}$
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	$V_{(BR)}$	5	40		V
Junction capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_j$		30		pF
Radiant intensity	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$I_e$	7	15	35	mW/sr
	$I_F = 1.5\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$		140		mW/sr
Radiant power	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\phi_e$		20		mW
Temperature coefficient of $\phi_e$	$I_F = 20\text{ mA}$	$TK_{\phi_e}$		-0.8		%/K
Angle of half intensity		$\phi$		$\pm 18$		deg
Peak wavelength	$I_F = 100\text{ mA}$	$\lambda_p$		950		nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		50		nm
Temperature coefficient of $\lambda_p$	$I_F = 100\text{ mA}$	$TK_{\lambda_p}$		0.2		nm/K
Rise time	$I_F = 100\text{ mA}$	$t_r$		800		ns
	$I_F = 1.5\text{ A}$	$t_r$		400		ns
Fall time	$I_F = 100\text{ mA}$	$t_f$		800		ns
	$I_F = 1.5\text{ A}$	$t_f$		400		ns
Virtual source diameter		$d$		2.1		mm

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

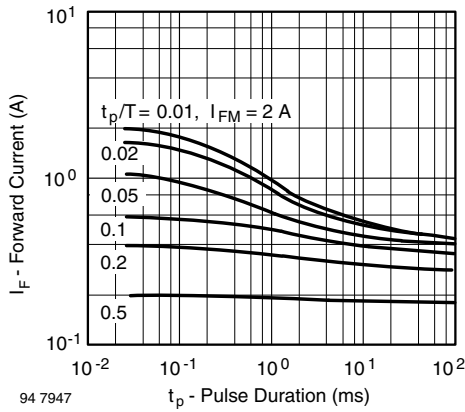


Fig. 3 - Pulse Forward Current vs. Pulse Duration

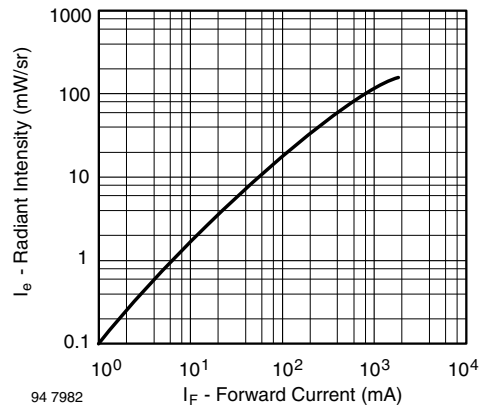


Fig. 6 - Radiant Intensity vs. Forward Current

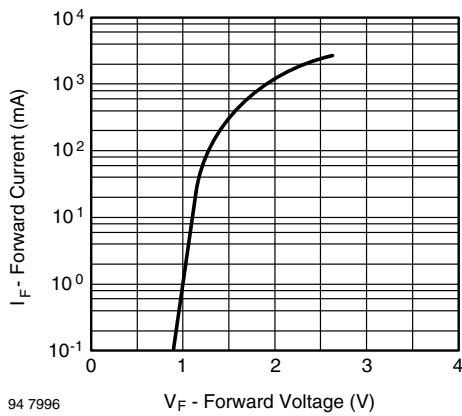


Fig. 4 - Forward Current vs. Forward Voltage

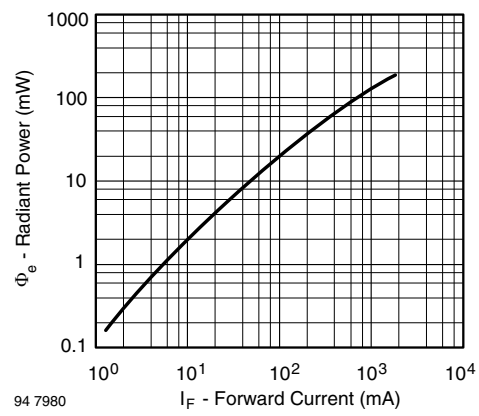


Fig. 7 - Radiant Power vs. Forward Current

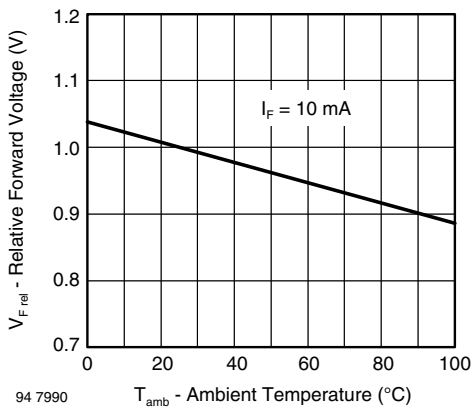


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

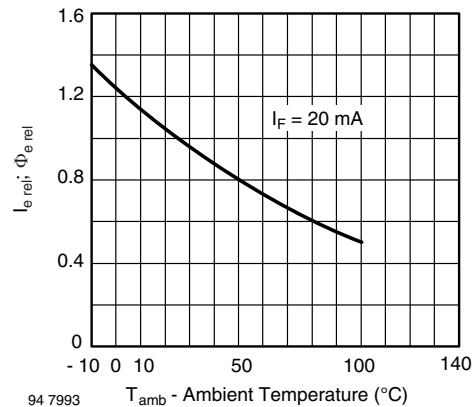


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

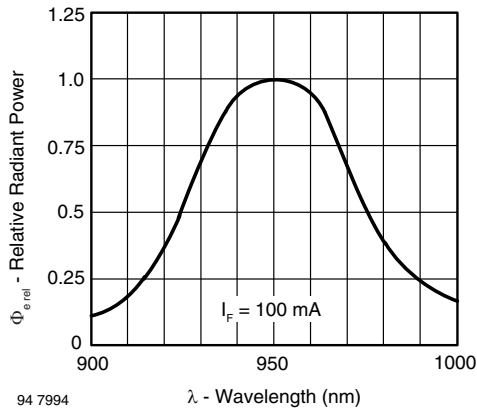


Fig. 9 - Relative Radiant Power vs. Wavelength

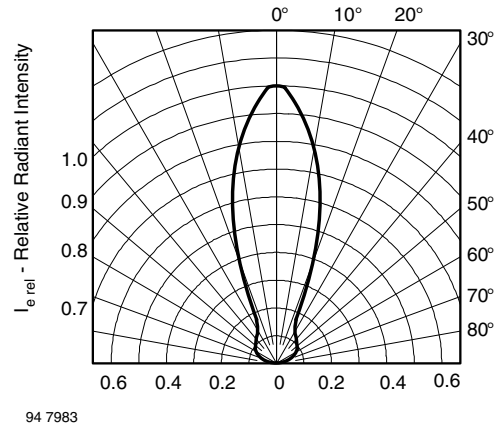
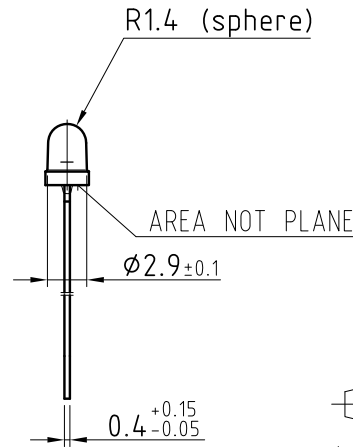
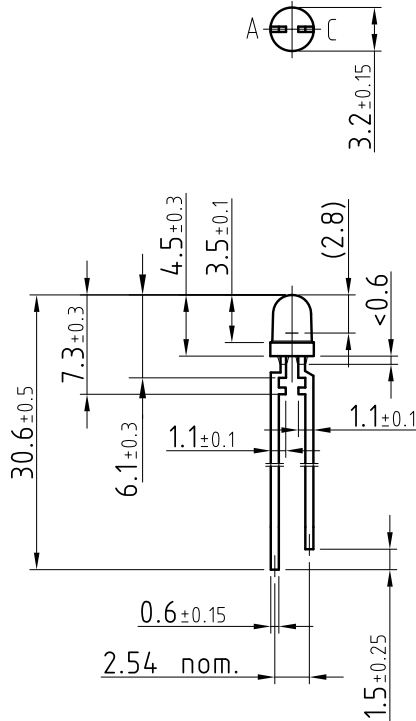


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

**PACKAGE DIMENSIONS** in millimeters



technical drawings according to DIN specifications

Drawing-No.: 6.544-5256.02-4  
 Issue: 2; 19.05.98  
 95 10915



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